2, 4, and 8-Channel Low Capacitance ESD Protection Arrays

Features

- 2, 4, and 8 channels of ESD protection
- Provides ESD protection to IEC61000-4-2
 8kV contact discharge
 - 15kV air discharge
- Low loading capacitance of 2.0pF max.
- Low clamping voltage

IMC

- Channel I/O to I/O capacitance 1.5pF typical
- Zener diode protects supply rail and eliminates the need for external by-pass capacitors
- Each I/O pin can withstand over 1000 ESD strikes
- Available in SOT, and MSOP packages
- Lead-free version available

Applications

- DVI ports, HDMI ports in notebooks, set top boxes, digital TVs, LCD displays
- Serial ATA ports in desktop PCs and hard disk drives
- PCI Express ports
- General purpose high-speed data line ESD protection

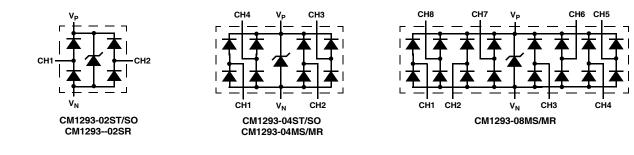
Product Description

The CM1293 family of diode arrays has been designed to provide ESD protection for electronic components or sub-systems requiring minimal capacitive loading. These devices are ideal for protecting systems with high data and clock rates or for circuits requiring low capacitive loading. Each ESD channel consists of a pair of diodes in series which steer the positive or negative ESD current pulse to either the positive (VP) or negative (V_N) supply rail. A Zener diode is embedded between V_P and V_N, offering two advantages. First, it protects the V_{CC} rail against ESD strikes, and second, it eliminates the need for a bypass capacitor that would otherwise be needed for absorbing positive ESD strikes to ground. The CM1293 will protect against ESD pulses up to (±15kV air, ±8kV contact discharge) per the IEC 61000-4-2 Level 4 standard.

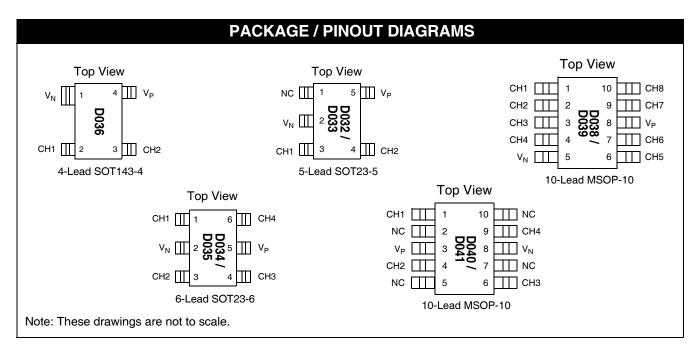
This device is particularly well-suited for protecting systems using high-speed ports such as USB2.0, IEEE1394 (Firewire®, iLinkTM), Serial ATA, DVI, HDMI and corresponding ports in removable storage, digital camcorders, DVD-RW drives and other applications where extremely low loading capacitance with ESD protection are required in a small package footprint.

The CM1293 family of devices is available with optional lead-free finishing.

Electrical Schematics







PIN DESCRIPTIONS					
2-CHANNEL, 4-LEAD SOT143-4 PACKAGE					
PIN	NAME	TYPE	PIN		
1	V _N	GND	1		
2	CH1	I/O	2		
3	CH2	I/O	3		
4	VP	PWR	4		
	2	-CHANNEL, 5-L	EAD SOT23-5 PACKAGE		
PIN	NAME	TYPE	DESCRIPTION		
1	NC		No connect		
2	V _N	GND	Negative voltage supply rail		
3	CH1	I/O	ESD Channel		
4	CH2	I/O	ESD Channel		
5	VP	PWR	Positive voltage supply rail		
	4	-CHANNEL, 6-L	EAD SOT23-6 PACKAGE		
PIN	NAME	TYPE	DESCRIPTION		
1	CH1	I/O	ESD Channel		
2	V _N	GND	Negative voltage supply rail		
3	CH2	I/O	ESD Channel		
4	CH3	I/O	ESD Channel		
5	V _P	PWR	Positive voltage supply rail		
6	CH4	I/O	ESD Channel		
5	VP	PWR	Positive voltage supply rail		
6	CH4	I/O	ESD Channel		

4-CHANNEL, 10-LEAD MSOP-10 PACKAGE						
PIN	NAME	TYPE	DESCRIPTION			
1	CH1	I/O	ESD Channel			
2	NC		No connect			
3	VP	PWR	Positive voltage supply rail			
4	CH2	I/O	ESD Channel			
5	NC		No connect			
6	CH3	I/O	ESD Channel			
7	NC		No connect			
8	V _N	GND	Negative voltage supply rail			
9	CH4	I/O	ESD Channel			
10	NC		No connect			
	8-0	CHANNEL, 10-I	EAD MSOP-10 PACKAGE			
PIN	NAME	TYPE	DESCRIPTION			
1	CH1	I/O	ESD Channel			
2	CH2	I/O	ESD Channel			
3	CH3	I/O	ESD Channel			
4	CH4	I/O	ESD Channel			
5	V _N	PWR	Positive voltage supply rail			
6	CH5	I/O	ESD Channel			
7	CH6	I/O	ESD Channel			
8	V _N	GND	Negative voltage supply rail			
9	CH7	I/O	ESD Channel			
10	CH8	I/O	ESD Channel			

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Ordering Information

PART NUMBERING INFORMATION							
	Standard Finish Lead-free Finish					e Finish	
# of Channels	Leads	Package	Ordering Part Number ¹	Part Marking	Ordering Part Number ¹	Part Marking	
2	4	SOT143-4			CM1293-02SR	D036	
2	5	SOT23-5	CM1293-02ST	D032	CM1293-02SO	D033	
4	6	SOT23-6	CM1293-04ST	D034	CM1293-04SO	D035	
4	10	MSOP-10	CM1293-04MS	D040	CM1293-04MR	D041	
8	10	MSOP-10	CM1293-08MS	D038	CM1293-08MR	D039	

Note 1: Parts are shipped in Tape & Reel form unless otherwise specified.

Specifications

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	RATING	UNITS			
Operating Supply Voltage (V _P - V _N)	6.0	V			
Operating Temperature Range	-40 to +85	°C			
Storage Temperature Range	-65 to +150	°C			
DC Voltage at any channel input	(V _N - 0.5) to (V _P + 0.5)	V			

STANDARD OPERATING CONDITIONS					
PARAMETER	RATING	UNITS			
Operating Temperature Range	-40 to +85	°C			
Package Power Rating SOT143-4 Package (CM1293-02SR) SOT23-5 Package (CM1293-02ST/SO) SOT23-6 Package (CM1293-04ST/SO) MSOP-10 Package (CM1293-04MS/MR) MSOP-10 Package (CM1293-08MS/MR)	225 225 225 400 400	mW mW mW mW			

Specifications (cont'd)

	ELECTRICAL OPERATING CHARACTERISTICS ¹						
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _P	Operating Supply Voltage (V_P - V_N)			3.3	5.5	V	
۱ _Р	Operating Supply Current	(V _P -V _N)=3.3V			8.0	μA	
V _F	Diode Forward Voltage Top Diode Bottom Diode	I _F = 8mA; T _A =25°C	0.60 0.60	0.80 0.80	0.95 0.95	V V	
I _{LEAK}	Channel Leakage Current	T _A =25°C; V _P =5V, V _N =0V		±0.1	±1.0	μA	
C _{IN}	Channel Input Capacitance	At 1 MHz, V _P =3.3V, V _N =0V, V _{IN} =1.65V; Note 2			2.0	pF	
Δc_{IO}	Channel I/O to I/O capacitance			1.5		pF	
V _{ESD}	ESD Protection Peak Discharge Voltage at any channel input, in system						
	a) Contact discharge per IEC 61000-4-2 standard	Notes 2, 4 & 5; T _A =25°C	±8			kV	
	b) Human Body Model, MIL-STD-883, Method 3015	Notes 2, 3 & 5; T _A =25°C	±15			kV	
V _{CL}	Channel Clamp Voltage Positive Transients Negative Transients	At 8kV ESD HBM; T _A =25°C; Notes 2 & 3		+9.0 -9.0		V V	
R _{DYN}	Dynamic Resistance Positive Transients Negative Transients	T _A =25°C; Notes 5 & 6		1.2 0.6		Ω Ω	

Note 1: All parameters specified at $T_A = -40^{\circ}C$ to $+85^{\circ}C$ unless otherwise noted.

Note 2: These parameters guaranteed by design and characterization.

Note 3: Human Body Model per MIL-STD-883, Method 3015, C_{Discharge} = 100pF, R_{Discharge} = 1.5KQ, V_P = 3.3V, V_N grounded.

Note 4: Standard IEC 61000-4-2 with C_{Discharge} = 150pF, R_{Discharge} = 330Ω , V_P = 3.3V, V_N grounded.

Note 5: These measurements performed with no external capacitor on V_P.

Note 6: Measured under pulsed conditions, pulse width = 0.7mS, maximum current = 1.5A.

Performance Information (Cont'd)

Typical Filter Performance (nominal conditions unless specified otherwise, 50 Ohm Environment)

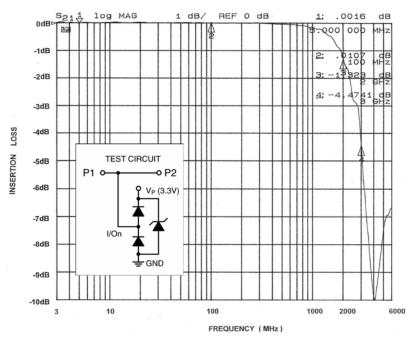


Figure 1. Insertion Loss (S21) VS. Frequency (0V DC Bias, V_P=3.3V)

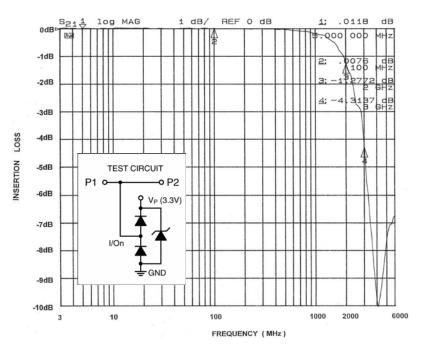


Figure 2. Insertion Loss (S21) VS. Frequency (2.5V DC Bias, V_P=3.3V)

Application Information

Design Considerations

In order to realize the maximum protection against ESD pulses, care must be taken in the PCB layout to minimize parasitic series inductances on the Supply/ Ground rails as well as the signal trace segment between the signal input (typically a connector) and the ESD protection device. Refer to Figure 3, which illustrates an example of a positive ESD pulse striking an input channel. The parasitic series inductance back to the power supply is represented by L_1 and L_2 . The voltage V_{CL} on the line being protected is:

 $V_{CL} = Fwd voltage drop of D_1 + V_{SUPPLY} + L_1 x d(I_{ESD}) / dt$ + L₂ x d(I_{ESD}) / dt

where I_{ESD} is the ESD current pulse, and V_{SUPPLY} is the positive supply voltage.

An ESD current pulse can rise from zero to its peak value in a very short time. As an example, a level 4 contact discharge per the IEC61000-4-2 standard results in a current pulse that rises from zero to 30 Amps in 1ns. Here $d(I_{ESD})/dt$ can be approximated by

 $\Delta I_{ESD}/\Delta t$, or 30/(1x10⁻⁹). So just 10nH of series inductance (L₁ and L₂ combined) will lead to a 300V increment in V_{CI}!

Similarly for negative ESD pulses, parasitic series inductance from the V_N pin to the ground rail will lead to drastically increased negative voltage on the line being protected.

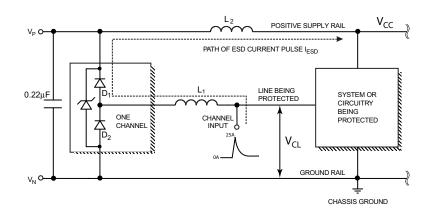
The CM1293 has an integrated Zener diode between V_{P} and $V_{\text{N}}.$ This greatly reduces the effect of supply rail

inductance L₂ on V_{CL} by clamping V_P at the breakdown voltage of the Zener diode. However, for the lowest possible V_{CL}, especially when V_P is biased at a voltage significantly below the Zener breakdown voltage, it is recommended that a 0.22 μ F ceramic chip capacitor be connected between V_P and the ground plane.

As a general rule, the ESD Protection Array should be located as close as possible to the point of entry of expected electrostatic discharges. The power supply bypass capacitor mentioned above should be as close to the V_P pin of the Protection Array as possible, with minimum PCB trace lengths to the power supply, ground planes and between the signal input and the ESD device to minimize stray series inductance.

Additional Information

See also California Micro Devices Application Note AP209, "Design Considerations for ESD Protection", in the Applications section at www.calmicro.com.





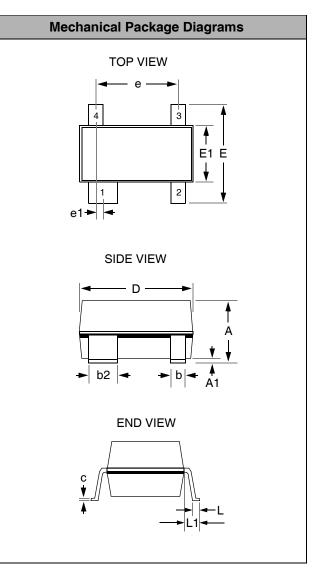
Mechanical Details

SOT143 Mechanical Specifications

Dimensions for CM1293-02SR devices supplied in 4pin SOT143 packages are presented below.

For complete information on the SOT143, see the California Micro Devices SOT143 Package Information document.

PACKAGE DIMENSIONS						
Package		SOT143				
Pins			4			
Dimensions	Millir	neters	Inc	hes		
Dimensions	Min	Max	Min	Max		
Α	0.80	1.22	0.031	0.048		
A1	0.05	0.15	0.002	0.006		
b	0.30	0.50	0.012	0.019		
b2	0.76	0.89	0.030 0.03			
с	0.08	0.20	0.003	0.008		
D	2.80	3.04	0.110	0.119		
E	2.10	2.64	0.082	0.103		
E1	1.20	1.40	0.047	0.055		
е	1.92	BSC	0.07	5 BSC		
e1	0.20) BSC	0.00	B BSC		
L	0.4	0.6	0.016	0.024		
L1	0.54 REF 0.021 REF					
# per tape and reel	3000 pieces					
C	Controlling dimension: millimeters					



Package Dimensions for SOT143.

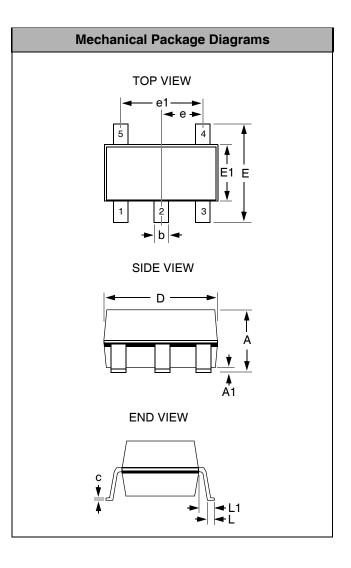
Mechanical Details (cont'd)

SOT23-5 Mechanical Specifications

Dimensions for CM1293-02ST/SO devices packaged in 5-pin SOT23 packages are presented below.

For complete information on the SOT23-5 package, see the California Micro Devices SOT23 Package Information document.

PACKAGE DIMENSIONS						
Package	SOT2	3-5 (JEDEC	c name is M	IO-178)		
Pins			5			
Dimensions	Millir	neters	Inches			
Dimensions	Min	Max	Min	Max		
Α		1.45		0.0571		
A1	0.00	0.15	0.0000	0.0059		
b	0.30	0.50	0.0118	0.0197		
с	0.08	0.22	0.0031	0.0087		
D	2.75	3.05	0.1083 0.1201			
E	2.60	3.00	0.1024	0.1181		
E1	1.45	1.75	0.0571	0.0689		
е	0.95	5 BSC	0.037	4 BSC		
e1	1.90) BSC	0.074	8 BSC		
L	0.30	0.60	0.0118	0.0236		
L1	0.60 REF 0.0236 REF					
# per tape and reel	3000 pieces					
C	Controlling dimension: millimeters					



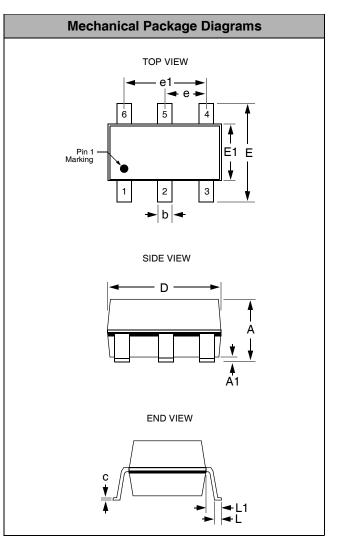
Mechanical Details (cont'd)

SOT23-6 Mechanical Specifications

CM1293-04ST/SO devices are packaged in 6-pin SOT23 packages. Dimensions are presented below.

For complete information on the SOT23-6 package, see the California Micro Devices SOT23 Package Information document.

PACKAGE DIMENSIONS						
Package	SOT2	3-6 (JEDEC	c name is N	IO-178)		
Pins			6			
Dimensions	Millir	neters	Inches			
Dimensions	Min	Max	Min	Мах		
Α		1.45		0.0571		
A1	0.00	0.15	0.0000	0.0059		
b	0.30	0.50	0.0118	0.0197		
с	0.08	0.22	0.0031	0.0087		
D	2.75	3.05	0.1083 0.120			
E	2.60	3.00	0.1024 0.1181			
E1	1.45	1.75	0.0571	0.0689		
е	0.95	5 BSC	0.037	'4 BSC		
e1	1.90) BSC	0.074	8 BSC		
L	0.30	0.60	0.0118	0.0236		
L1	0.60 REF 0.0236 REF					
# per tape and reel	3000 pieces					
C	Controlling dimension: millimeters					



Package Dimensions for SOT23-6.

Mechanical Details (cont'd)

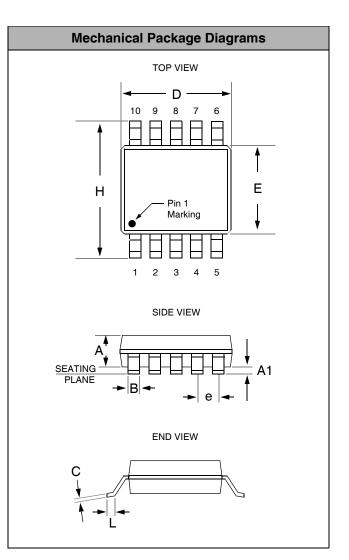
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MSOP-10 Mechanical Specifications

CM1293-04MS/MR and CM1293-08MS/MR devices are packaged in 10-pin MSOP packages. Dimensions are presented below.

For complete information on the MSOP-10 package, see the California Micro Devices MSOP Package Information document.

PACKAGE DIMENSIONS						
Package		MS	SOP			
Pins		1	10			
Dimensions	Millir	neters	Inc	hes		
Dimensions	Min	Max	Min	Max		
Α	0.75	0.95	0.028	0.038		
A1	0.05	0.15	0.002	0.006		
В	0.18	0.40	0.006	0.016		
С	0	.18	0.	007		
D	2.90	3.10	0.114	0.122		
E	2.90	3.10	0.114	0.122		
е	0.50) BSC	0.019	6 BSC		
Н	4.76	5.00	0.187	0.197		
L	0.40	0.70	0.0137	0.029		
# per tape and reel	4000					
	Controlling dimension: inches					



Package Dimensions for MSOP-10